

SANGDEST **MICROELECTRONICS**

SDURF1040CT(CTR)

Technical Data Data Sheet N0175, Rev. A

Green Products

SDURF1040CT(CTR) ULTRAFAST PLASTIC RECTIFIER

Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- **Snubber diode**
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

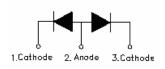
Features:

- Fully Molded Isolation
- **Ultra-Fast Recovery**
- Low Forward Voltage Drop
- High Surge Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot

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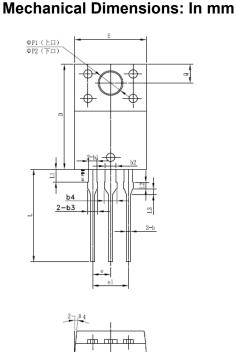
Additional testing can be offered upon request

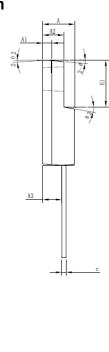




SDURF1040CT

SDURF1040CTR





SYMBOL	MIN.	TYP.	MAX.
А	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3 b	2.50	2.70	3.20 2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
С	0.55	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
е		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦΡ1(上口)	3.30	3.50	3.70
ΦΡ2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

ITO-220AB



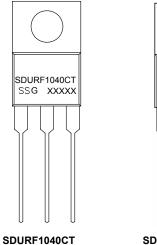
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Marking Diagram:



SDURF 1040CTR SSG XXXXX

Where XXXXX is YYWWL

SDUR	= Device Type
F	= Package Type
10	= Forward Current (10A)
40	= Reverse Voltage (400V)
CT/CTR	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SDURF1040CT/CTR	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	400	V
Average Forward Current	Io _(AV)	50% duty cycle T _C =112℃, rectangular wave form	10	A
Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	80	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop(per leg)	V_{F}	@ I _F = 5A, Pulse, T _J = 25℃	1.3	V
Reverse Current	I _R	@V _R = rated V _R T _J = 25℃	30	μA
Reverse Recovery Time	t _{rr}	I_F =500mA, I_R =1A,and I_{rm} =250mA	45	ns

* Pulse width < 300 μ s, duty cycle < 2%

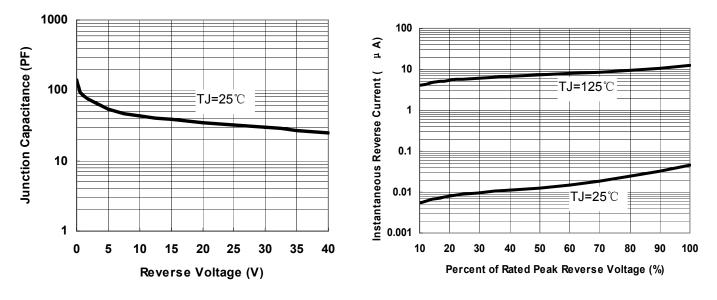
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	3.5	°C /W
Approximate Weight	wt	-	2	g
Case Style		ITO-220AB		



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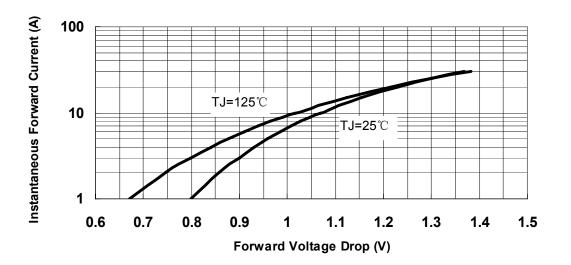


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

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